Amendments to the Claims:

This list of claims will replace all prior versions, and listings, of claims in the application

Claim 1 (Currently Amended): A method for manufacturing metal lines of a semiconductor device, the method comprising the steps of:

forming a first interlayer insulating film exposing a top portion of a lower metal line on a semiconductor substrate;

forming a stacked structure of a first etch barrier film, a second interlayer insulating film, a second etch barrier film, a third interlayer insulating film and an anti-reflection film;

etching the stacked structure to form a via contact hole exposing a portion of the first etch barrier film on the lower metal line;

removing the exposed portion of the first etch barrier film to expose the lower metal line;

forming a photoresist film on the entire surface of the exposed lower metal line, the via contact hole, and the remaining antireflection film;

subjecting the photoresist film to an exposure and development process using an upper metal line mask to form a photoresist film pattern for defining an upper metal line region, wherein the photoresist film pattern further fills a portion of the via contact hole to cover the exposed lower metal line;

etching the anti-reflection film and the third interlayer insulating film using the photoresist film pattern as a mask to form the upper metal line region;

removing the photoresist film pattern; and

after the photoresist film pattern is removed, forming an upper metal line contacting the lower metal line by filling the upper metal line region.

Claim 2 (Original): The method according to claim 1, wherein the first and the second etch barrier films comprise a film selected from the group consisting of SiN film, SiC film and SiCN film, respectively.

Claim 3 (Previously Presented): The method according to claim 1, wherein the second and the

third interlayer insulating films comprise a film selected from the group consisting of a silica-base low-k film and a silica-base porous low-k film, respectively.

Claim 4 (Previously Presented): The method according to claim 1, wherein the second and the third interlayer insulating films comprise a film selected from the group consisting of an oxide film, an organic low-k film, an organic porous low-k film and combinations thereof, respectively.

Claim 5 (Original): The method according to claim 1, wherein the anti-reflection film comprises a SiON inorganic anti-reflection film.

Claim 6 (Original): The method according to claim 1, wherein the step of etching the anti-reflection film and the third interlayer insulating film is a plasma etching process using a mixture gas of $CF_4/O_2/Ar$.

Claim 7 (Original): The method according to claim 6, wherein the step of removing the photoresist film pattern in the via contact hole is performed in in-situ manner.